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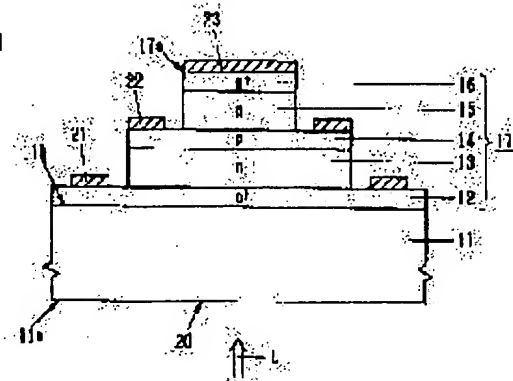
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(57)Abstract:

PURPOSE: To obtain high efficiency in photoelectric conversion by forming an electrode layer, which serves also as a reflecting layer and located on the upper side of a semiconductor laminated layer other than the side nearer to the substrate, without alloying it with the semiconductor laminated layer so that the light, which passes through an absorbing part, can be used effectively.

CONSTITUTION: A semiconductor light receiver comprises a semiconductor substrate 11 and a semiconductor laminated layer, which includes first semiconductor layers 12 and 13 of first conductive type, a semiconductor layer 14 of secondary conductive type, and third semiconductor layers 15 and 16 of first conductive type. Moreover, a first electrode layer 21 for the first semiconductor layers 12 and 13, and a secondary electrode 23 for the third semiconductor layers 15 and 16 are provided in the semiconductor light receiver. The rear side 11a of the semiconductor substrate 11 other than the side facing a semiconductor laminated layer 17 is used as a light incident face 20. At the same time, a secondary electrode layer 23, which serves also as a reflecting layer and is located on the upper side 17a of the semiconductor laminated layer 17 other than the side nearer to the semiconductor substrate 11, is formed without alloying it with the semiconductor laminated layer 17.



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